

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON) \max}$	$I_D \max$ $T_A = +25^\circ\text{C}$
30V	57m Ω @ $V_{GS} = 10\text{V}$	6.0A
	112m Ω @ $V_{GS} = 4.5\text{V}$	3.8A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

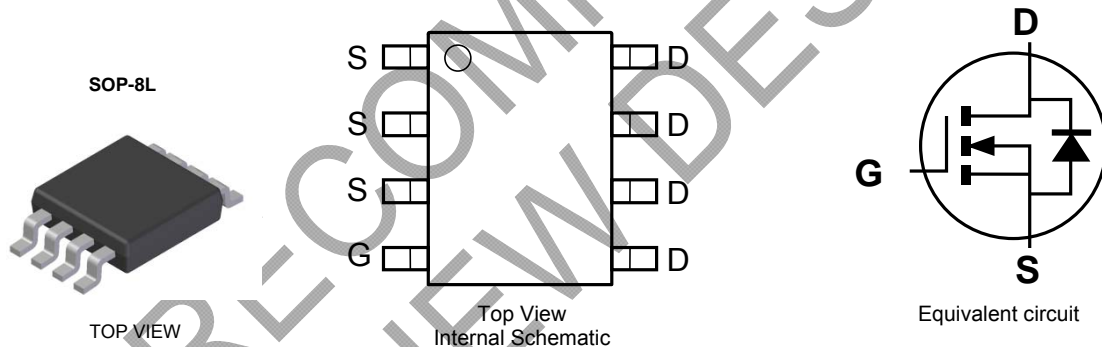
- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOP-8L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.074g (Approximate)

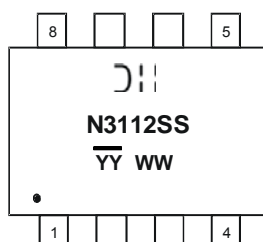


Ordering Information (Note 4)

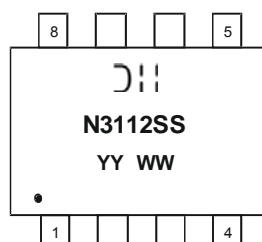
Part Number	Case	Packaging
DMN3112SSS-13	SOP-8L	2,500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



Chengdu A/T Site



Shanghai A/T Site

- ⌋|| = Manufacturer's Marking
- N3112SS = Product Type Marking Code
- YYWW = Date Code Marking
- YY or YY = Year (ex: 13 = 2013)
- WW = Week (01 - 53)
- YY = Date Code Marking for SAT (Shanghai Assembly/ Test site)
- YY = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 20	V
Drain Current (Note 5)	Steady State	$T_A = +25^\circ\text{C}$	I_D	6	A
		$T_A = +70^\circ\text{C}$		4.5	
Pulsed Drain Current (Note 6)			I_{DM}	24	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	50	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	800	nA	$V_{DS} = 30\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 80	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$
		—	—	± 800		$V_{GS} = \pm 25\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	1	—	2.2	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	43	57	m Ω	$V_{GS} = 10\text{V}, I_D = 5.8\text{A}$
		—	83	112		$V_{GS} = 4.5\text{V}, I_D = 3.7\text{A}$
Forward Transconductance	g_{fs}	—	2.8	—	S	$V_{DS} = 10\text{V}, I_D = 3.7\text{A}$
Diode Forward Voltage (Note 7)	V_{SD}	0.5	0.8	1.2	V	$V_{GS} = 0\text{V}, I_S = 2.1\text{A}$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	268	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	73	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	50	—	pF	

- Notes:
- Device mounted on 2 oz copper pad layout with $R_{\theta JA} = 50^\circ\text{C/W}$.
 - Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.
 - Short duration pulse test used to minimize self-heating effect.

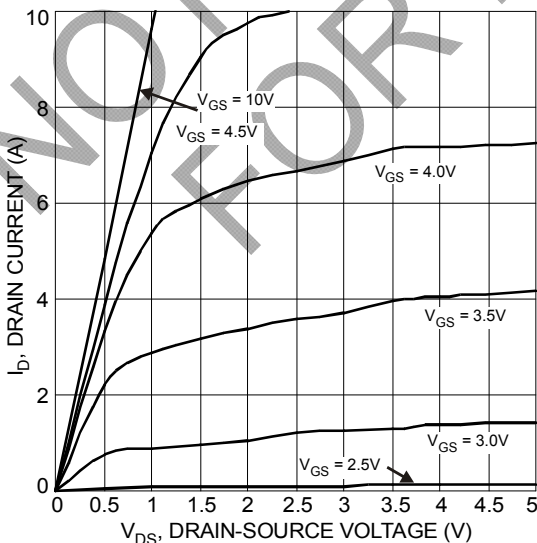


Fig. 1 Typical Output Characteristic

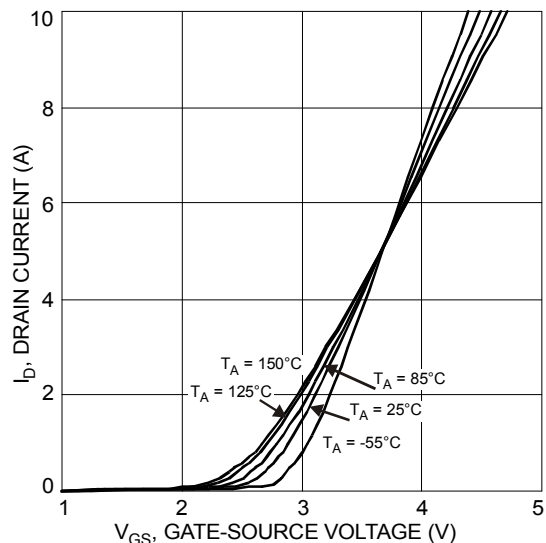


Fig. 2 Typical Transfer Characteristic

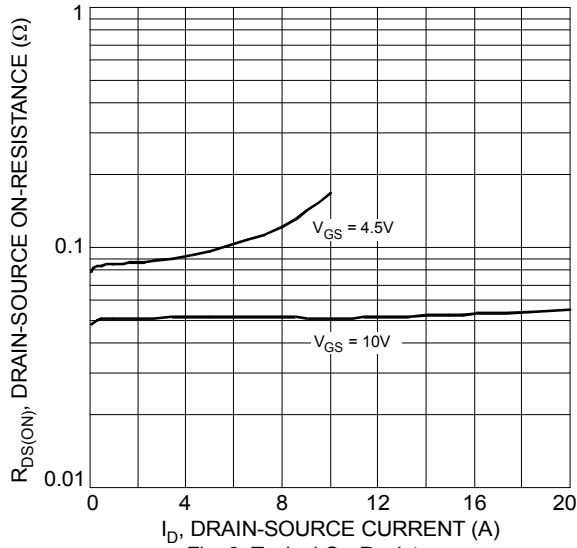


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

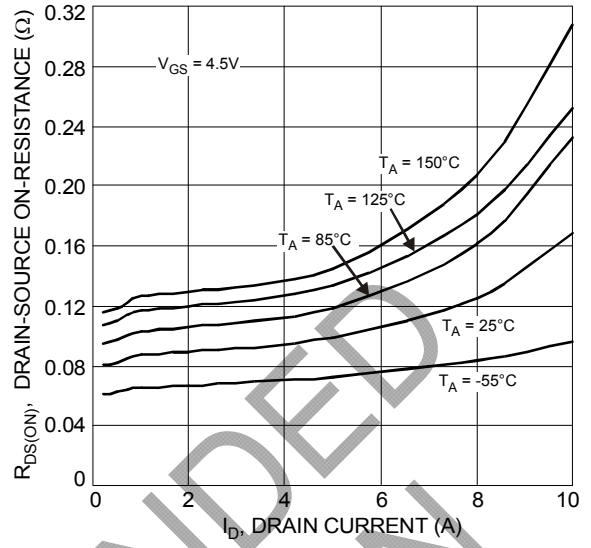


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

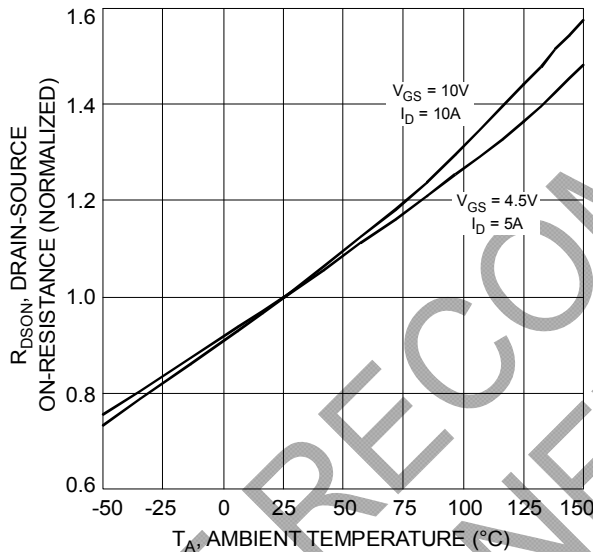


Fig. 5 On-Resistance Variation with Temperature

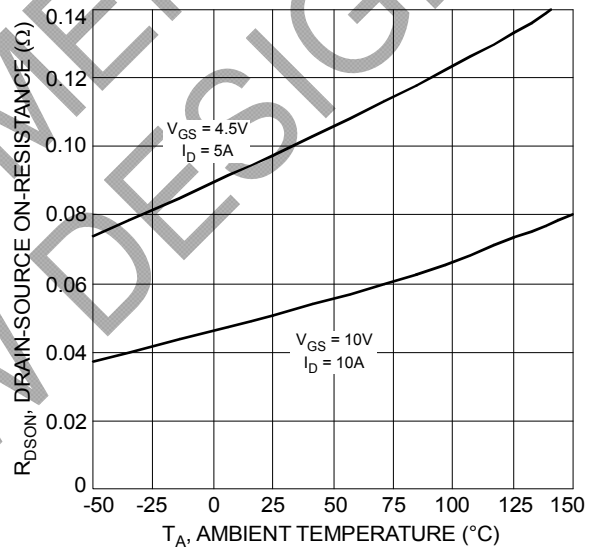


Fig. 6 On-Resistance Variation with Temperature

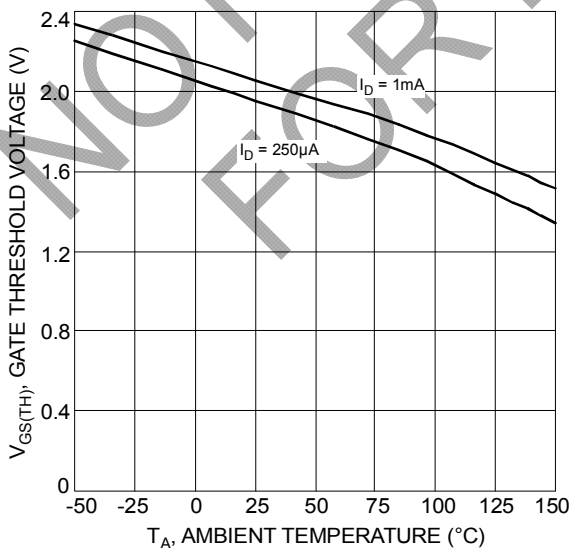


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

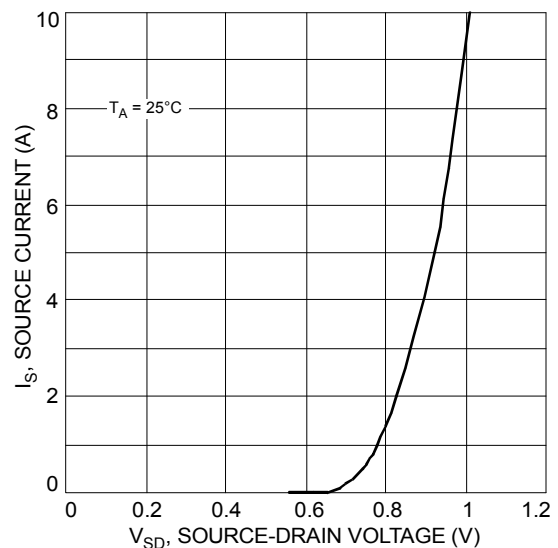


Fig. 8 Diode Forward Voltage vs. Current

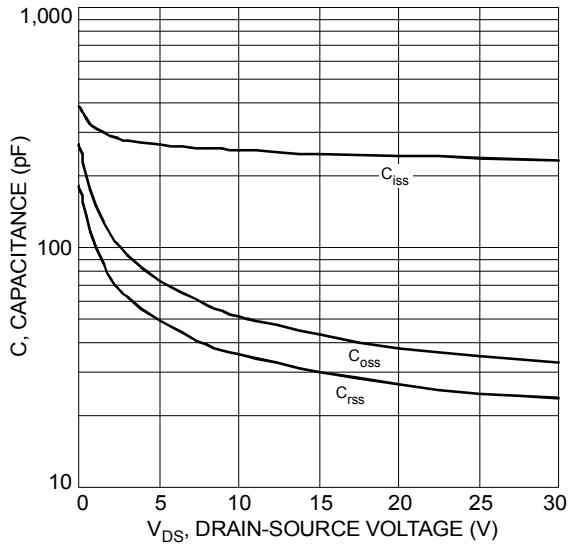


Fig. 9 Typical Total Capacitance

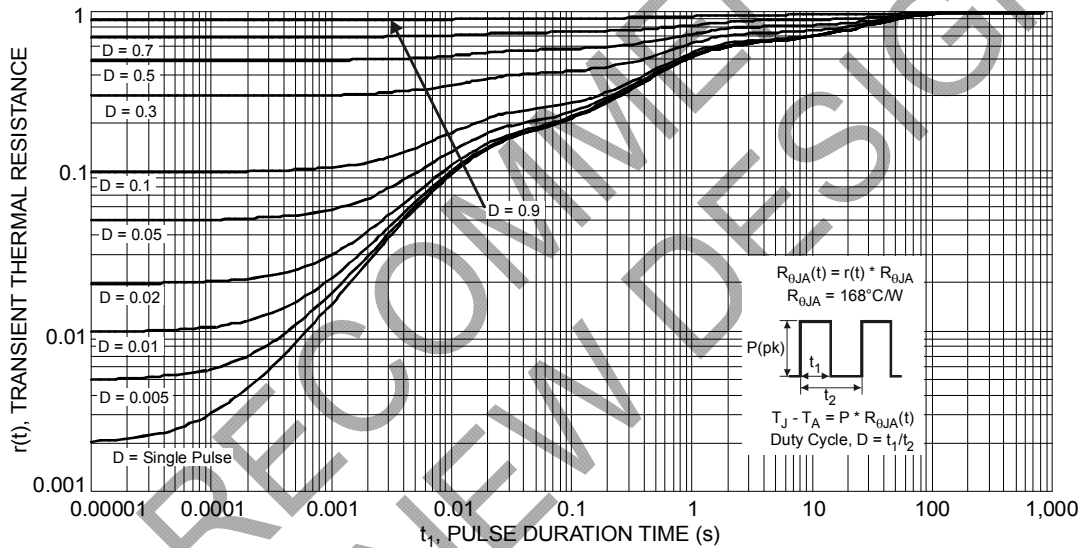
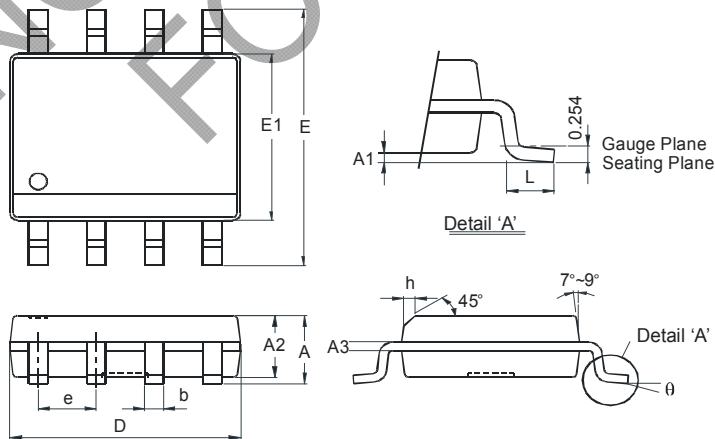


Fig. 10 Transient Thermal Response

Package Outline Dimensions

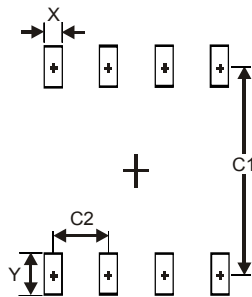
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOP-8L		
Dim	Min	Max
A	-	1.75
A1	0.08	0.25
A2	1.40	1.50
A3	0.20 Typ	
b	0.3	0.5
D	4.85	4.95
E	5.90	6.10
E1	3.80	3.90
e	1.27 Typ	
h	-	0.35
L	0.60	0.80
θ	0°	8°
All Dimensions in mm		

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
X	0.60
Y	1.55
C1	5.4
C2	1.27

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